ABSTRACT

A plasma treatment apparatus includes a wafer transfer tray having a first surface and a second surface opposite to the first surface and configured to hold a wafer on the first surface, a cooling unit configured to cool the wafer transfer tray, a conductive supporter configured to support the second surface of the wafer transfer tray, and a double-surface electrostatic attractor configured to electrostatically attract the wafer to the first surface of the wafer transfer tray and electrostatically attract the supporter to the second surface of the wafer transfer tray.